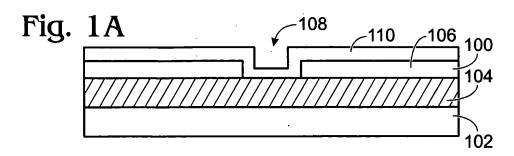
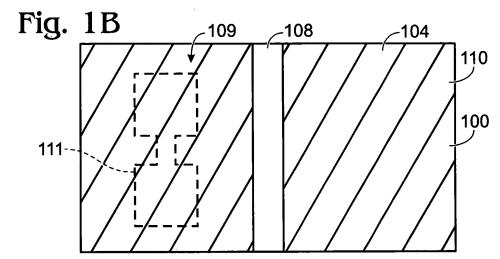
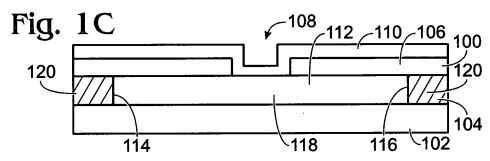
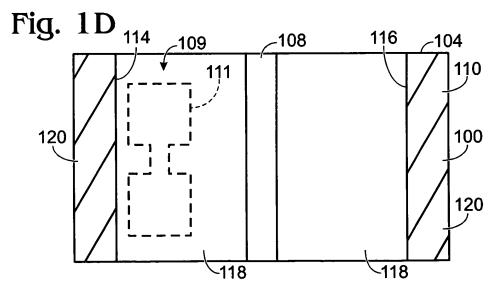
Semiconductor Device and a Method of Creating the Same Utilizing Metal Induced Crystallization While Suppressing Partial Solid Phase Crystallization Serial No.: 09/696,813

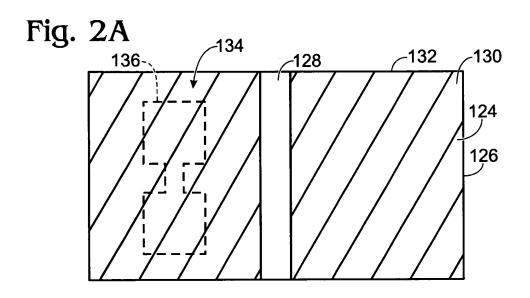
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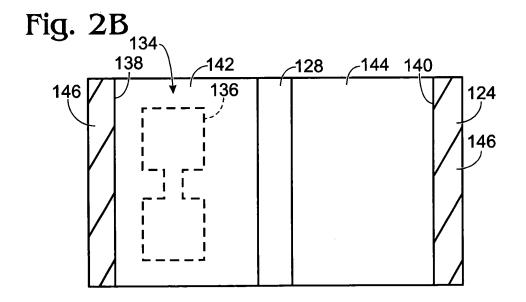




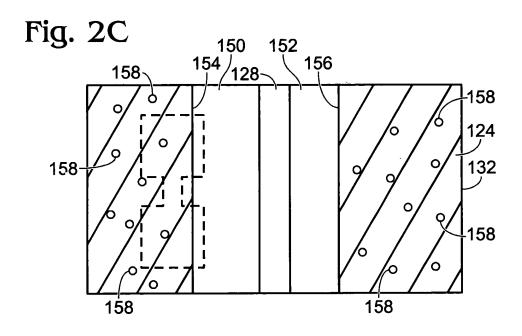


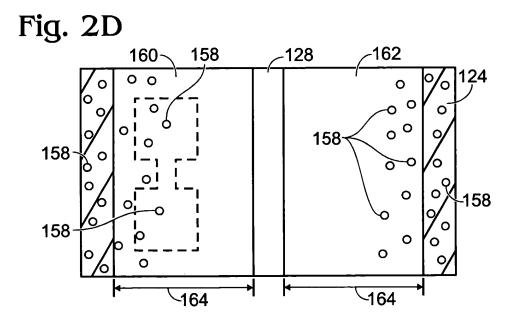






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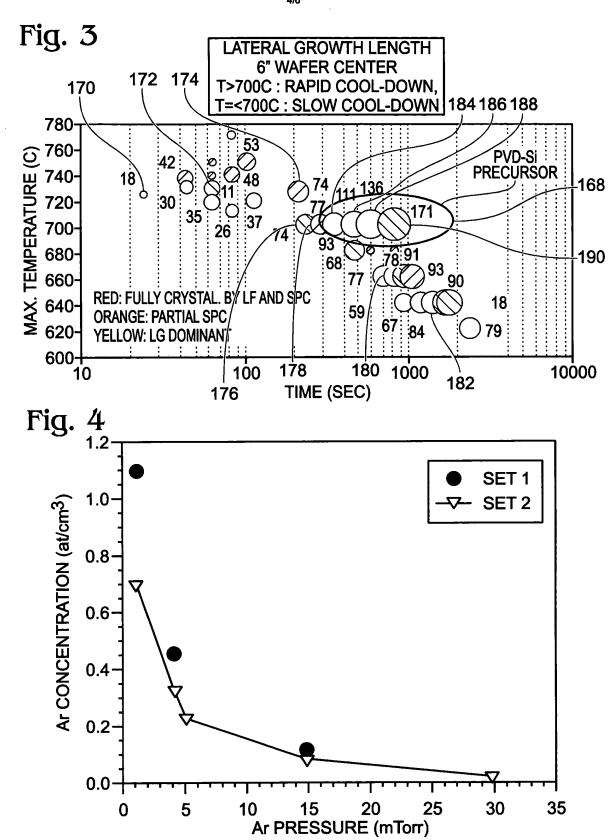


Fig. 5

POWER (kW)	PRESSURE (mTorr)	SPUTTERING GAS	Ar CONTENT (at/cm ³)
8	14-16	PURE He	<2X10 ¹⁸
		He/(3.8%)Ar	2-5X10 ¹⁸
		He/(10%)Ar	4-7X10 ¹⁸
		PURE Ar	6X10 ¹⁹
8	5-6	PURE Ar	2X10 ²⁰

